

To our customers,

Old Company Name in Catalogs and Other Documents

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Renesas Electronics website: <http://www.renesas.com>

April 1st, 2010
Renesas Electronics Corporation

Issued by: Renesas Electronics Corporation (<http://www.renesas.com>)

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EOL announced Product

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SWITCHING

N-CHANNEL POWER MOS FET

DESCRIPTION

The 2SK3575 is N-channel MOS FET device that features a low on-state resistance and excellent switching characteristics, designed for low voltage high current applications such as DC/DC converter with synchronous rectifier.

FEATURES

- 4.5V drive available
- Low on-state resistance
 $R_{DS(on)1} = 4.5 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 42 \text{ A)}$
- Low gate charge
 $Q_G = 70 \text{ nC TYP. (} V_{DD} = 24 \text{ V, } V_{GS} = 10 \text{ V, } I_D = 83 \text{ A)}$
- Avalanche capability ratings
- Surface mount device available

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Drain to Source Voltage ($V_{GS} = 0 \text{ V}$)	V_{DS}	30	V
Gate to Source Voltage ($V_{DS} = 0 \text{ V}$)	V_{GS}	± 20	V
Drain Current (DC) ($T_C = 25^\circ\text{C}$)	$I_{D(DC)}$	± 83	A
Drain Current (pulse) Note1	$I_{D(pulse)}$	± 332	A
Total Power Dissipation ($T_A = 25^\circ\text{C}$)	P_{T1}	1.5	W
Total Power Dissipation ($T_C = 25^\circ\text{C}$)	P_{T2}	105	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	$-55 \text{ to } +150$	$^\circ\text{C}$
Single Avalanche Current Note2	I_{AS}	57	A
Single Avalanche Energy Note2	E_{AS}	325	mJ

Notes 1. $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$

2. Starting $T_{ch} = 25^\circ\text{C}$, $V_{DD} = 15 \text{ V}$, $R_G = 25 \Omega$, $V_{GS} = 20 \rightarrow 0 \text{ V}$

★ ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK3575	TO-220AB
2SK3575-S	TO-262
2SK3575-ZK	TO-263
2SK3575-Z	TO-220SMD ^{Note}

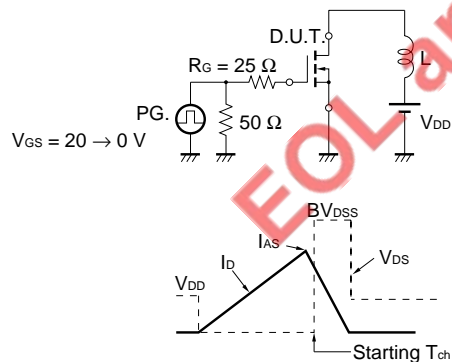
Note TO-220SMD package is produced only in Japan.

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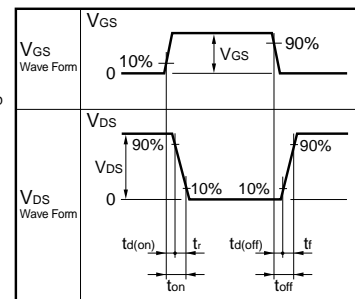
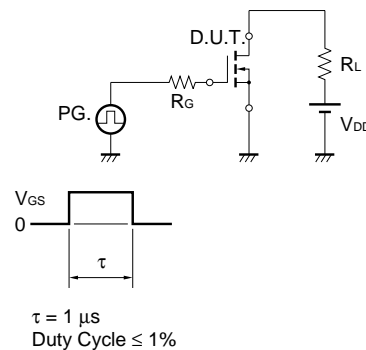
ELECTRICAL CHARACTERISTICS (T_A = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			10	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0 V			±100	nA
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	1.5		2.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} = 10 V, I _D = 42 A	27			S
Drain to Source On-state Resistance	R _{DS(on)1}	V _{GS} = 10 V, I _D = 42 A		3.3	4.5	mΩ
	R _{DS(on)2}	V _{GS} = 4.5 V, I _D = 42 A		4.3	6.4	mΩ
Input Capacitance	C _{iss}	V _{DS} = 10 V		3700		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		1430		pF
Reverse Transfer Capacitance	C _{rss}	f = 1 MHz		500		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 15 V, I _D = 42 A		26		ns
Rise Time	t _r	V _{GS} = 10 V		27		ns
Turn-off Delay Time	t _{d(off)}	R _G = 10 Ω		110		ns
Fall Time	t _f			40		ns
Total Gate Charge	Q _G	V _{DD} = 24 V		70		nC
Gate to Source Charge	Q _{GS}	V _{GS} = 10 V		12		nC
Gate to Drain Charge	Q _{GD}	I _D = 83 A		20		nC
Body Diode Forward Voltage	V _{F(S-D)}	I _F = 83 A, V _{GS} = 0 V		1.0		V
Reverse Recovery Time	t _{rr}	I _F = 83 A, V _{GS} = 0 V		61		ns
Reverse Recovery Charge	Q _{rr}	di/dt = 100 A/μs		94		nC

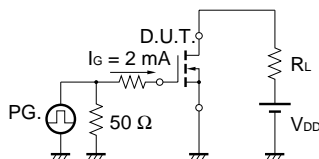
★ **TEST CIRCUIT 1 AVALANCHE CAPABILITY**



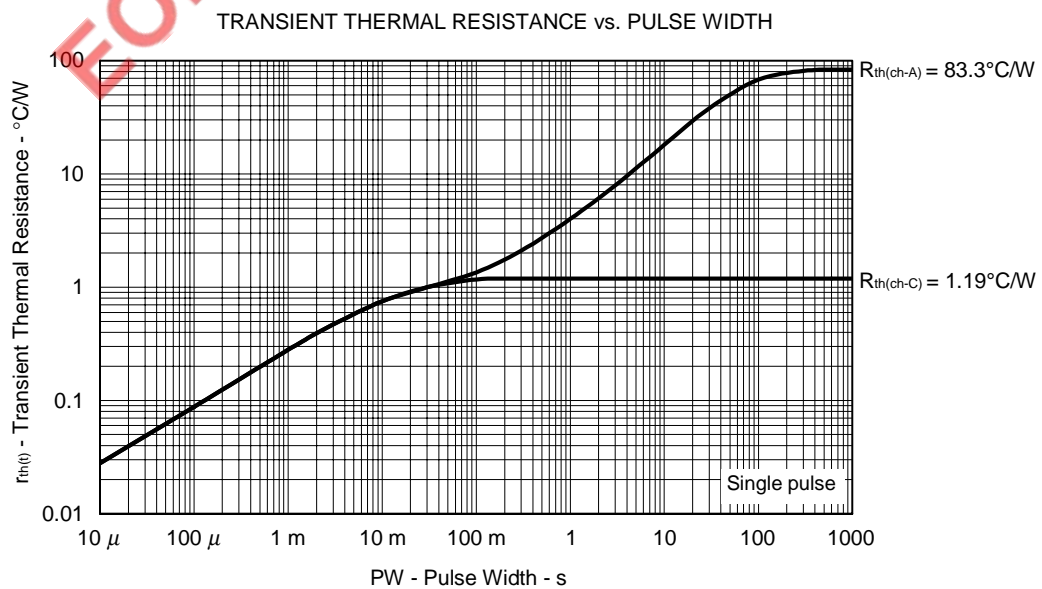
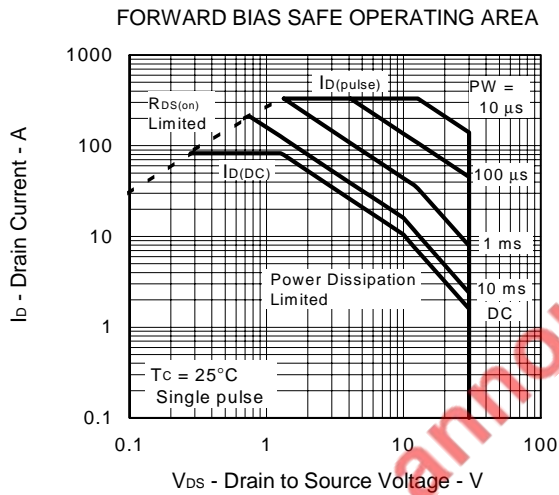
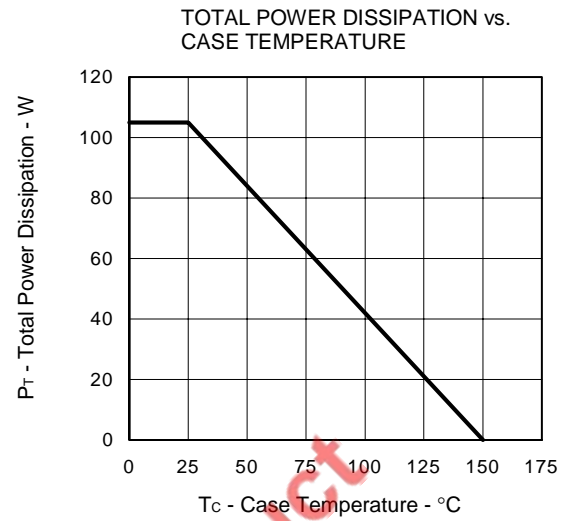
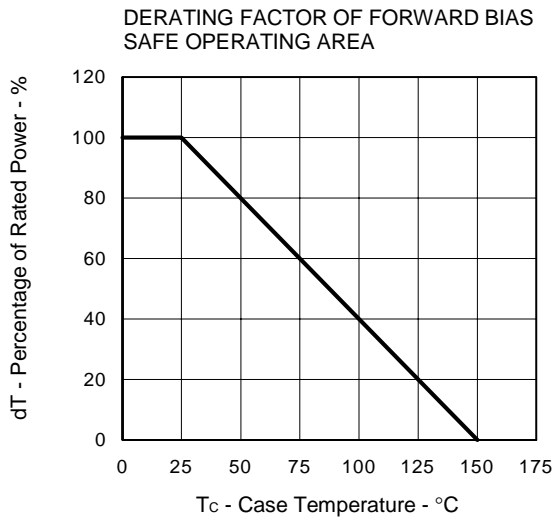
TEST CIRCUIT 2 SWITCHING TIME



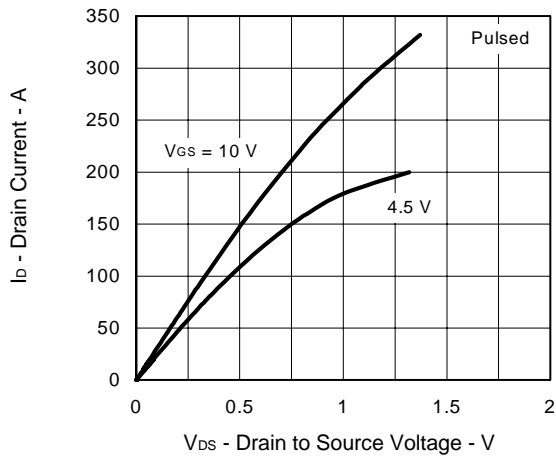
TEST CIRCUIT 3 GATE CHARGE



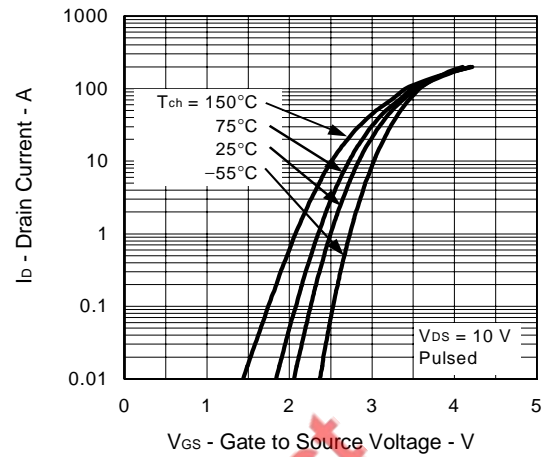
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)



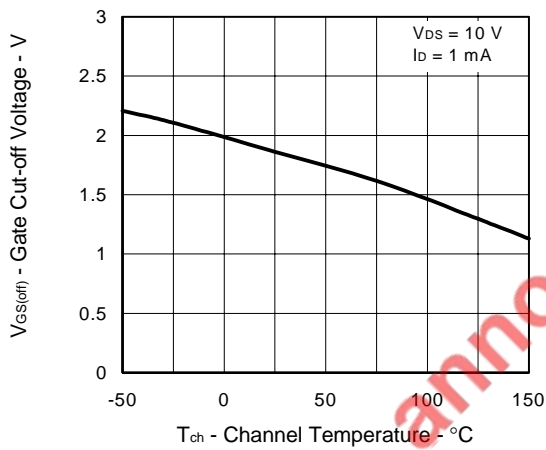
DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE



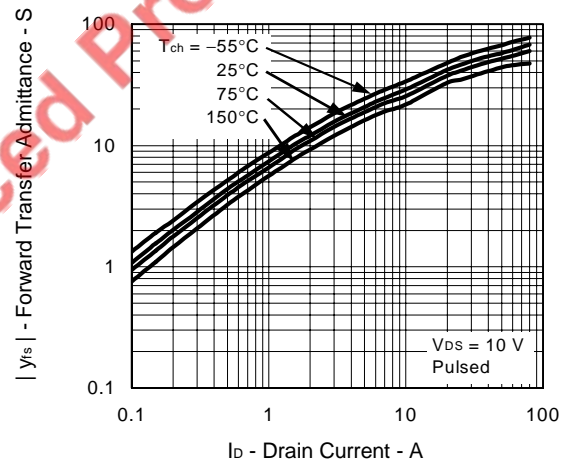
FORWARD TRANSFER CHARACTERISTICS



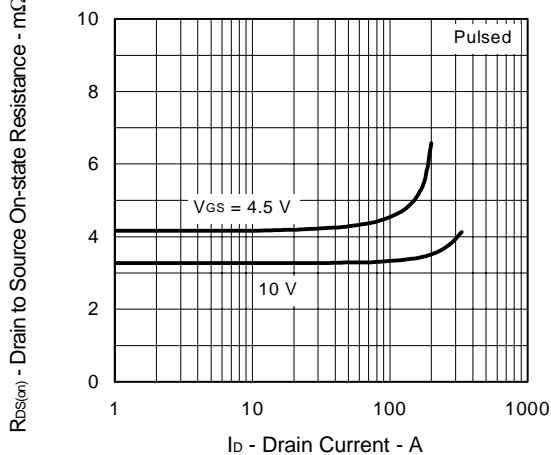
GATE CUT-OFF VOLTAGE vs.
CHANNEL TEMPERATURE



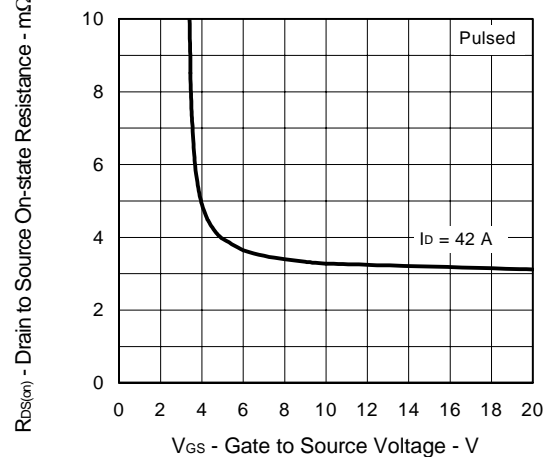
FORWARD TRANSFER ADMITTANCE vs.
DRAIN CURRENT



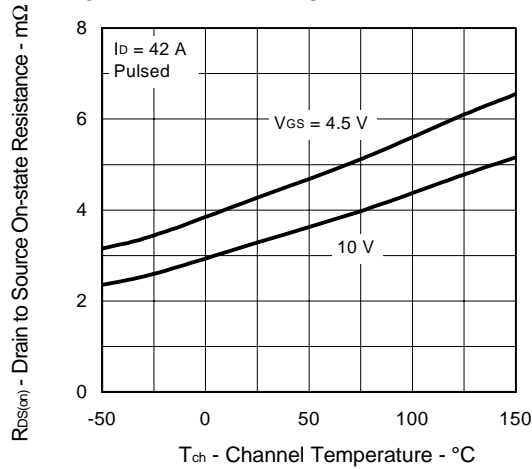
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
DRAIN CURRENT



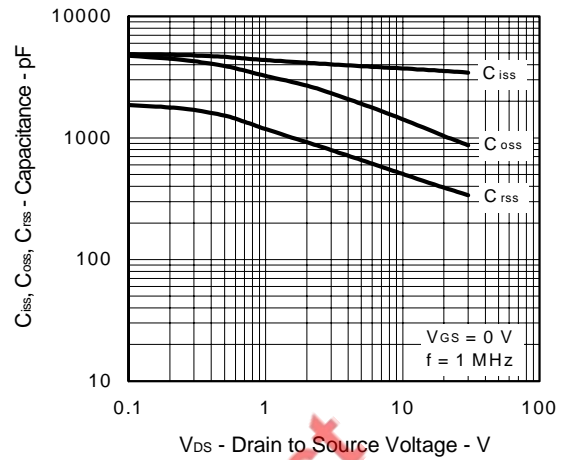
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE



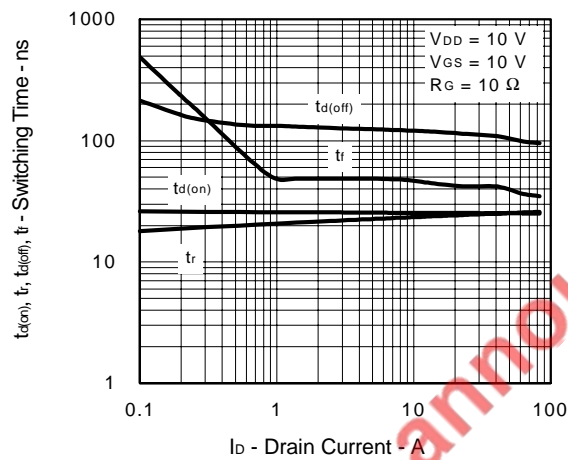
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



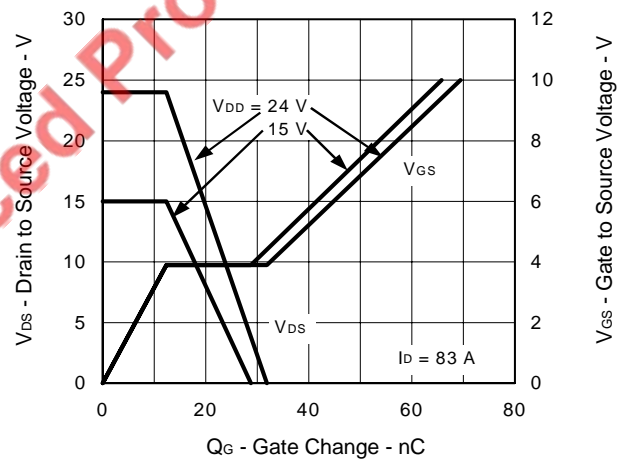
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



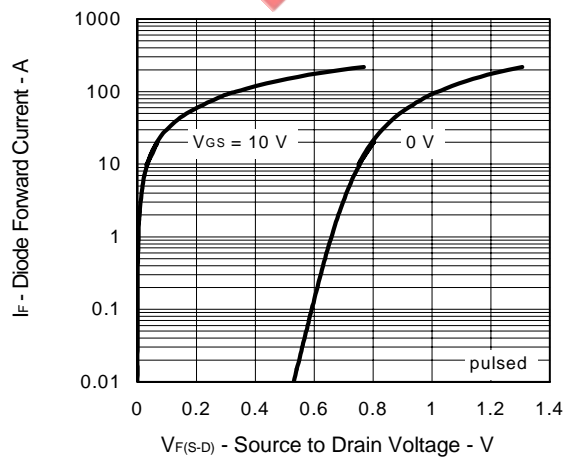
SWITCHING CHARACTERISTICS



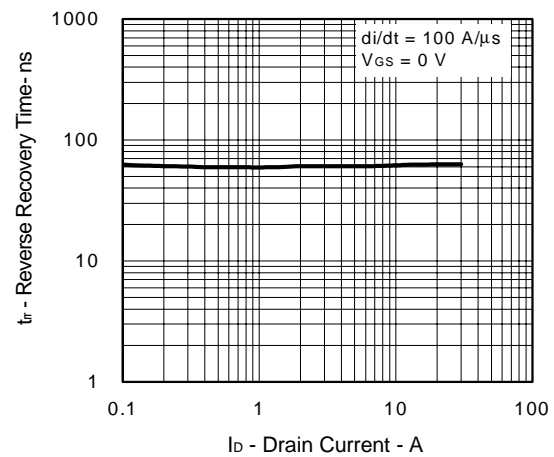
DYNAMIC INPUT/OUTPUT CHARACTERISTICS

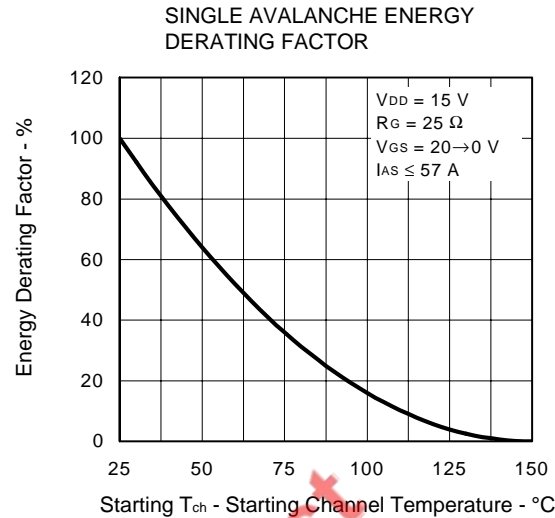
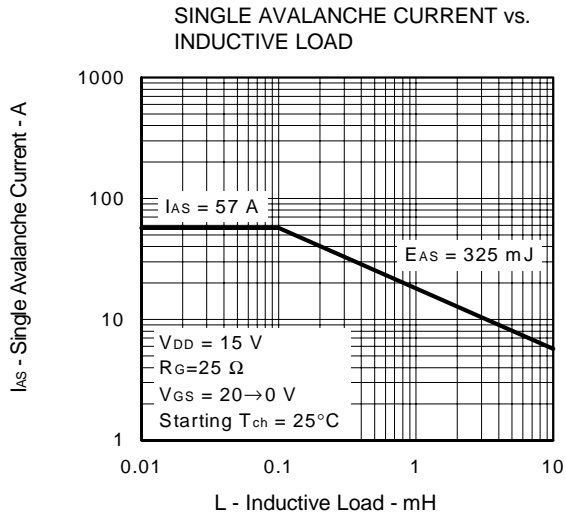


SOURCE TO DRAIN DIODE FORWARD VOLTAGE



REVERSE RECOVERY TIME vs. DRAIN CURRENT

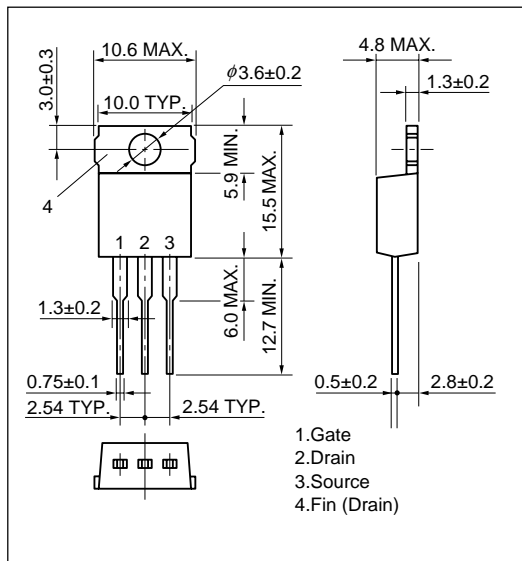




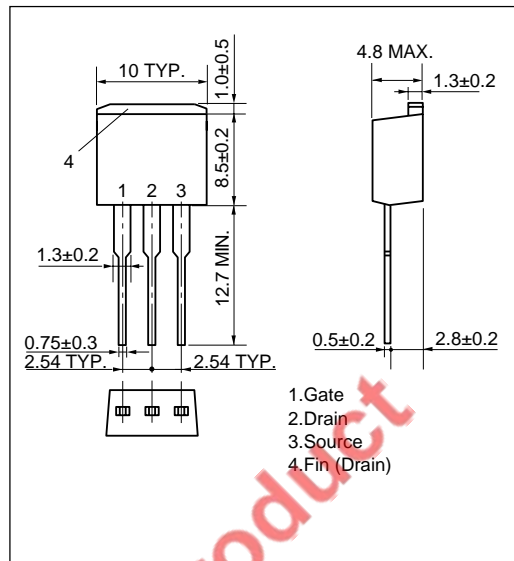
EOL announced Product

★ PACKAGE DRAWINGS (Unit: mm)

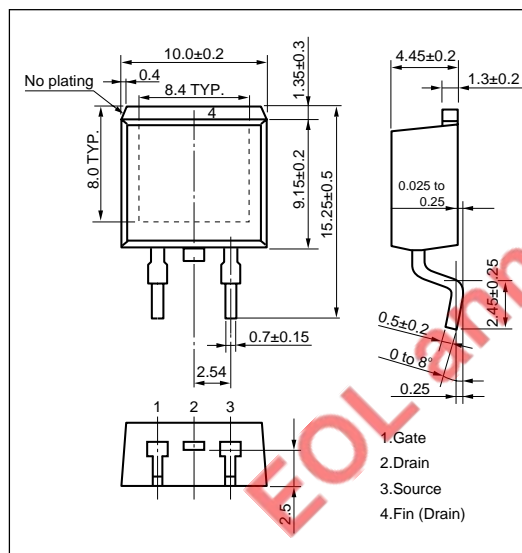
1) TO-220AB(MP-25)



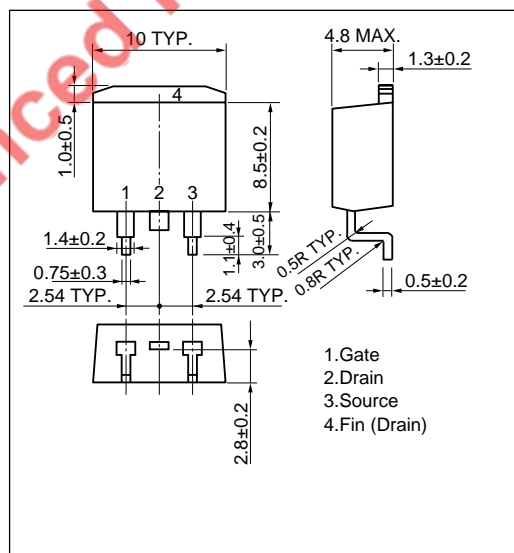
2) TO-262(MP-25 Fin Cut)



3) TO-263(MP-25ZK)

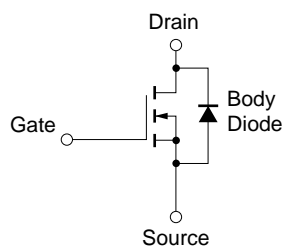


4) TO-220SMD(MP-25Z)^{Note}



Note This package is produced only in Japan.

EQUIVALENT CIRCUIT



Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

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